

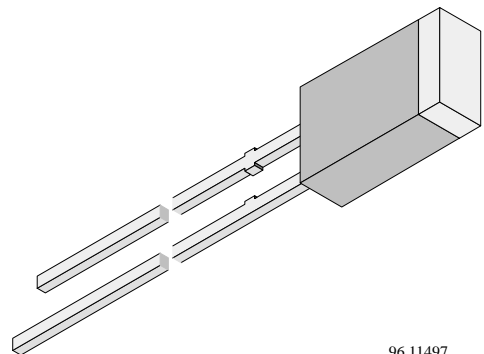
Symbol LED, 2.5 x 5 mm Flat Tinted Top-Diffused Package

| Color | Type | Technology | Angle of Half Intensity $\pm\varphi$ |
|--------|----------|--------------|---|
| Red | TLSH510. | GaAsP on GaP | 50° |
| Yellow | TLSY510. | GaAsP on GaP | 50° |
| Green | TLSG510. | GaP on GaP | 50° |

Description

This series was developed for use as compact surface display.

It is housed in a 2.5x5 mm rectangular molded package. This device has a flat tinted, top diffused package for uniform brightness when used in panels. The symbol LEDs are available in three bright colors: high efficiency red, yellow and green.



96 11497

Features

- Choice of three bright colors
- Uniform illumination
- Luminous intensity selected into groups
- Suitable for DC and pulse operation
- Flat light emitting surface
- Direct symbol indication is possible
- Yellow and green color categorized
- Wide viewing angle

Applications

Status lights
Background illumination
Maintenance lights
Indicator of audio and visual equipment
Off / On indicator
Readout lights
Legend lights
Illumination of moving boards

Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

TLSH510. , TLSY510. , TLSG510. ,

| Parameter | Test Conditions | Symbol | Value | Unit |
|-------------------------------------|---------------------------------------|------------|-------------|--------------------|
| Reverse voltage | | V_R | 6 | V |
| DC forward current | | I_F | 30 | mA |
| Surge forward current | $t_p \leq 10 \mu\text{s}$ | I_{FSM} | 1 | A |
| Power dissipation | $T_{amb} \leq 65^{\circ}\text{C}$ | P_V | 100 | mW |
| Junction temperature | | T_j | 100 | $^{\circ}\text{C}$ |
| Operating temperature range | | T_{amb} | -40 to +100 | $^{\circ}\text{C}$ |
| Storage temperature range | | T_{stg} | -55 to +100 | $^{\circ}\text{C}$ |
| Soldering temperature | $t \leq 5 \text{ s}$, 2 mm from body | T_{sd} | 260 | $^{\circ}\text{C}$ |
| Thermal resistance junction/ambient | | R_{thJA} | 350 | K/W |

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Red (TLSH510.)

| Parameter | Test Conditions | Type | Symbol | Min | Typ | Max | Unit |
|----------------------------------|-------------------------------|----------|-------------|------|----------|-----|------|
| Luminous intensity ¹⁾ | $I_F = 10\text{ mA}$ | TLSH5100 | I_V | 0.63 | 1.5 | | mcd |
| | | TLSH5101 | I_V | 1 | 2 | | mcd |
| Dominant wavelength | $I_F = 10\text{ mA}$ | | λ_d | | 640 | | nm |
| Peak wavelength | $I_F = 10\text{ mA}$ | | λ_p | | 650 | | nm |
| Angle of half intensity | $I_F = 10\text{ mA}$ | | ϕ | | ± 50 | | deg |
| Forward voltage | $I_F = 20\text{ mA}$ | | V_F | | 2 | 3 | V |
| Reverse voltage | $I_R = 10\text{ }\mu\text{A}$ | | V_R | 6 | 15 | | V |
| Junction capacitance | $V_R = 0, f = 1\text{ MHz}$ | | C_j | | 50 | | pF |

¹⁾ in one Packing Unit I_V Min./ I_V Max. ≤ 0.5

Yellow (TLSY510.)

| Parameter | Test Conditions | Type | Symbol | Min | Typ | Max | Unit |
|----------------------------------|-------------------------------|----------|-------------|-----|----------|-----|------|
| Luminous intensity ¹⁾ | $I_F = 10\text{ mA}$ | TLSY5100 | I_V | 0.4 | 1 | | mcd |
| | | TLSY5101 | I_V | 1 | 3 | | mcd |
| Dominant wavelength | $I_F = 10\text{ mA}$ | | λ_d | 581 | | 594 | nm |
| Peak wavelength | $I_F = 10\text{ mA}$ | | λ_p | | 585 | | nm |
| Angle of half intensity | $I_F = 10\text{ mA}$ | | ϕ | | ± 50 | | deg |
| Forward voltage | $I_F = 20\text{ mA}$ | | V_F | | 2.4 | 3 | V |
| Reverse voltage | $I_R = 10\text{ }\mu\text{A}$ | | V_R | 6 | 15 | | V |
| Junction capacitance | $V_R = 0, f = 1\text{ MHz}$ | | C_j | | 50 | | pF |

¹⁾ in one Packing Unit I_V Min./ I_V Max. ≤ 0.5

Green (TLSG510.)

| Parameter | Test Conditions | Type | Symbol | Min | Typ | Max | Unit |
|----------------------------------|-------------------------------|----------|-------------|-----|----------|-----|------|
| Luminous intensity ¹⁾ | $I_F = 10\text{ mA}$ | TLSG5100 | I_V | 0.4 | 1 | | mcd |
| | | TLSG5101 | I_V | 1 | 2 | | mcd |
| Dominant wavelength | $I_F = 10\text{ mA}$ | | λ_d | 562 | | 575 | nm |
| Peak wavelength | $I_F = 10\text{ mA}$ | | λ_p | | 565 | | nm |
| Angle of half intensity | $I_F = 10\text{ mA}$ | | ϕ | | ± 50 | | deg |
| Forward voltage | $I_F = 20\text{ mA}$ | | V_F | | 2.4 | 3 | V |
| Reverse voltage | $I_R = 10\text{ }\mu\text{A}$ | | V_R | 6 | 15 | | V |
| Junction capacitance | $V_R = 0, f = 1\text{ MHz}$ | | C_j | | 50 | | pF |

¹⁾ in one Packing Unit I_V Min./ I_V Max. ≤ 0.5

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

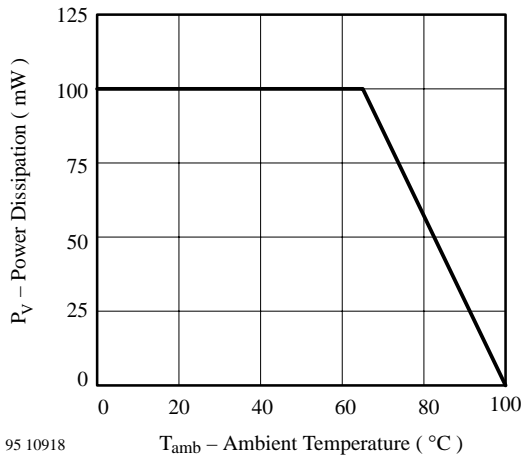


Figure 1. Power Dissipation vs. Ambient Temperature

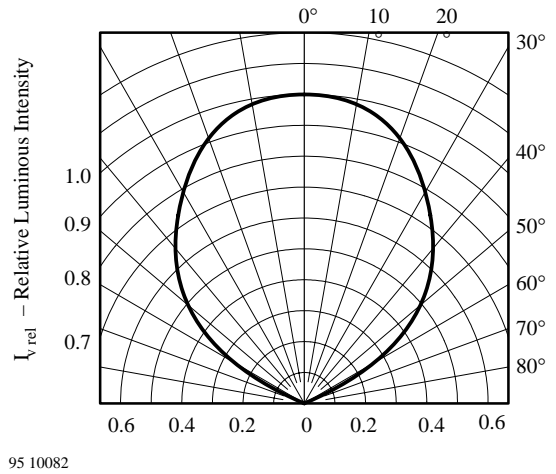


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

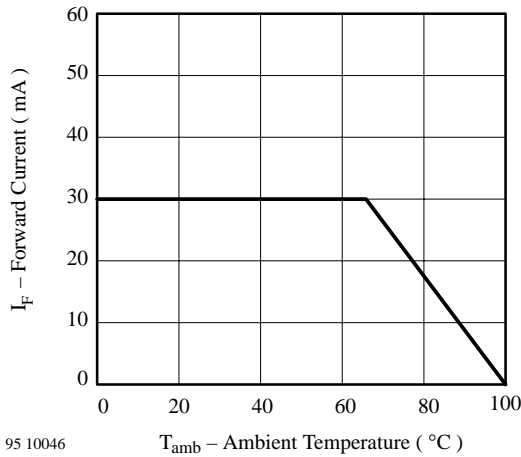


Figure 2. Forward Current vs. Ambient Temperature

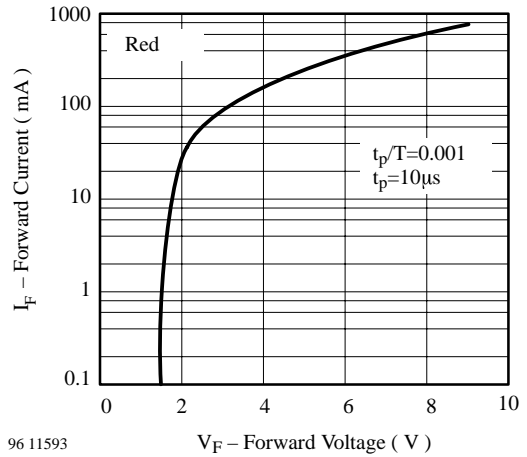


Figure 5. Forward Current vs. Forward Voltage

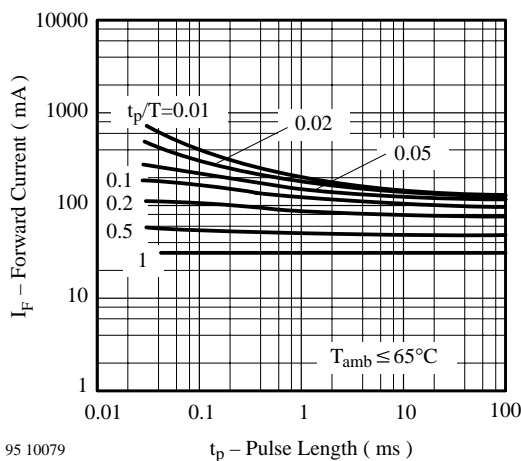


Figure 3. Forward Current vs. Pulse Length

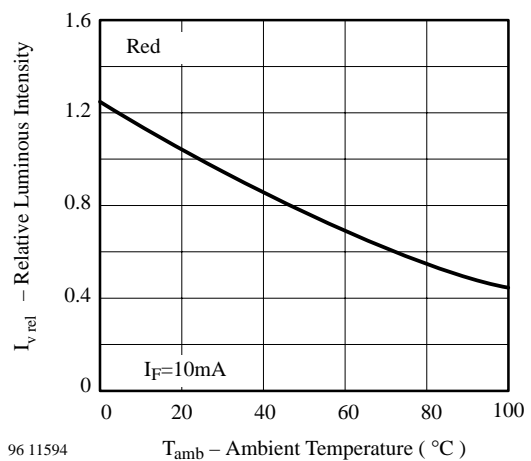


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature

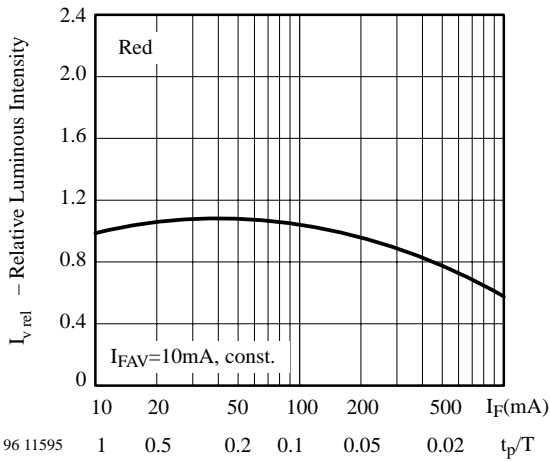


Figure 7. Rel. Lumin. Intensity vs. Forw. Current / Duty Cycle

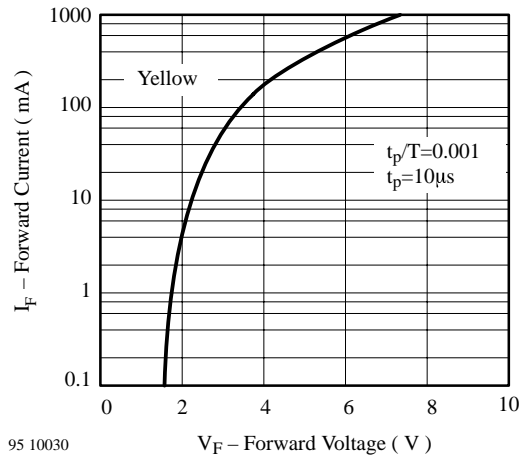


Figure 10. Forward Current vs. Forward Voltage

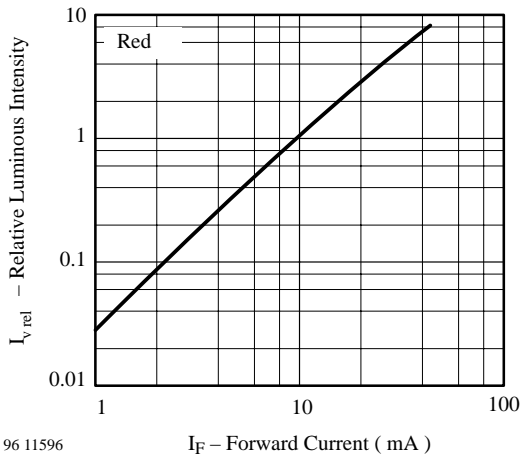


Figure 8. Rel. Luminous Intensity vs. Forward Current

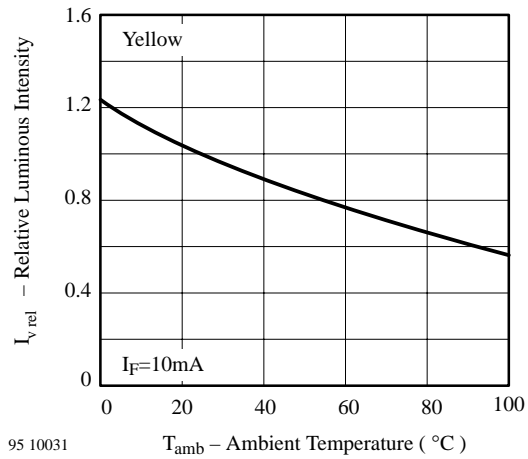


Figure 11. Rel. Luminous Intensity vs. Ambient Temperature

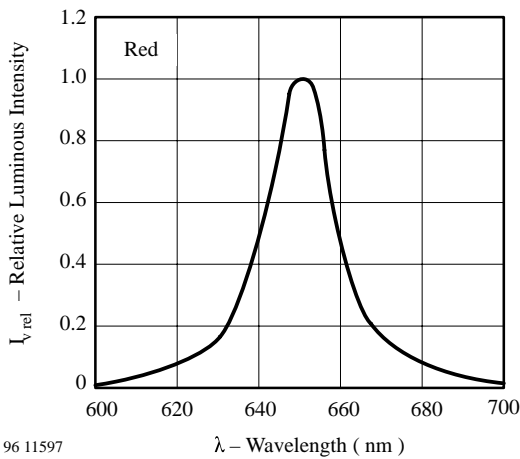


Figure 9. Rel. Luminous Intensity vs. Wavelength

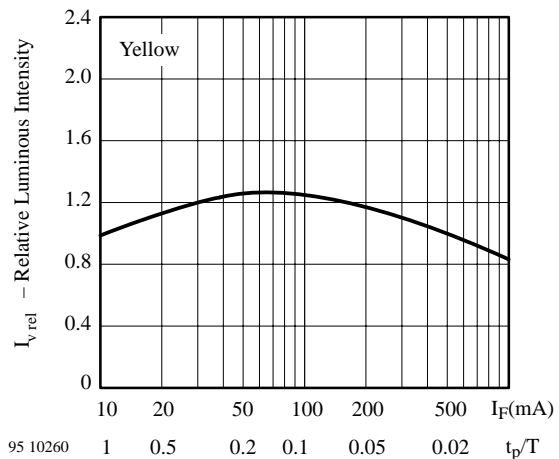
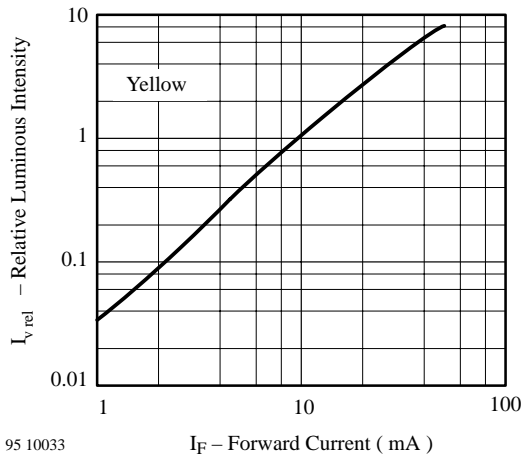
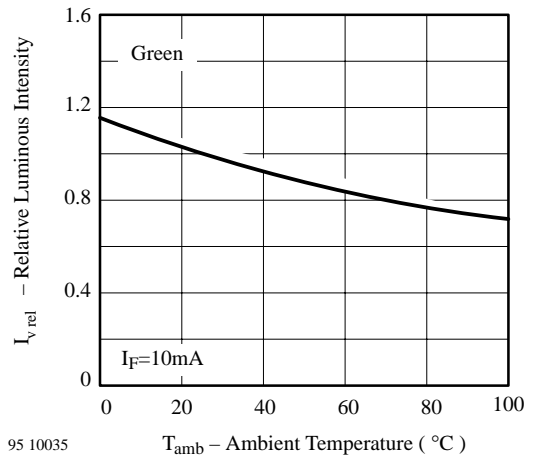


Figure 12. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle



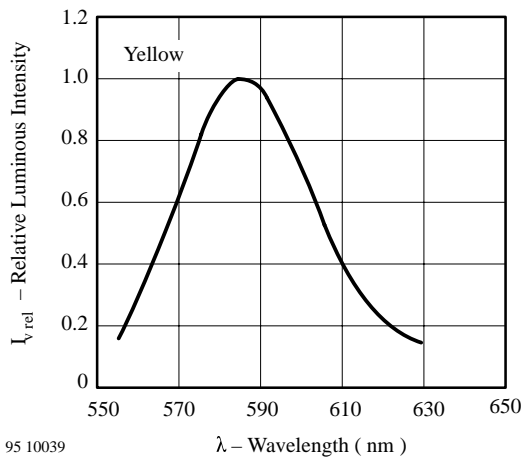
95 10033 I_F – Forward Current (mA)

Figure 13. Relative Luminous Intensity vs. Forward Current



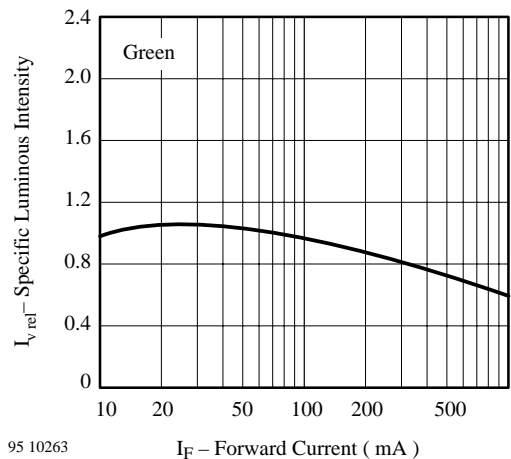
95 10035 T_{amb} – Ambient Temperature (°C)

Figure 16. Rel. Luminous Intensity vs. Ambient Temperature



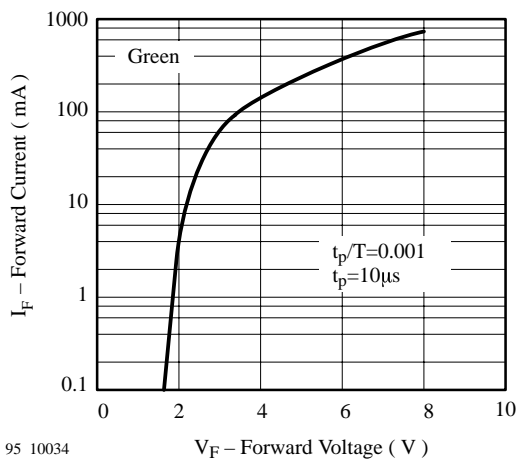
95 10039 λ – Wavelength (nm)

Figure 14. Relative Luminous Intensity vs. Wavelength



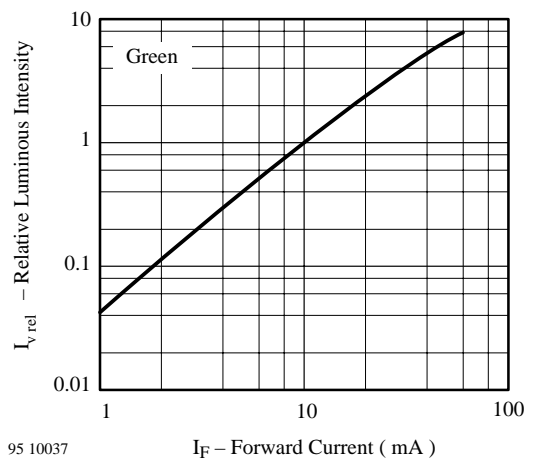
95 10263 I_F – Forward Current (mA)

Figure 17. Specific Luminous Intensity vs. Forward Current



95 10034 V_F – Forward Voltage (V)

Figure 15. Rel. Luminous Intensity vs. Ambient Temperature



95 10037 I_F – Forward Current (mA)

Figure 18. Relative Luminous Intensity vs. Forward Current

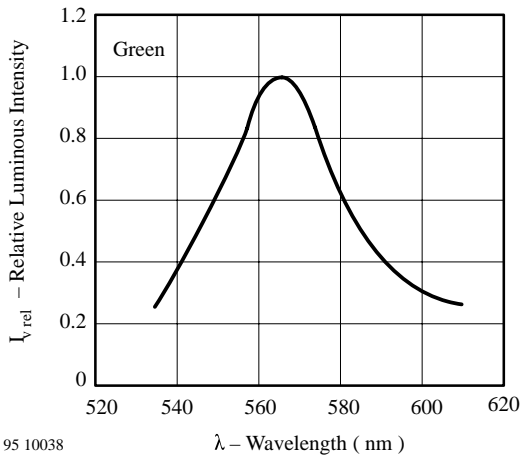
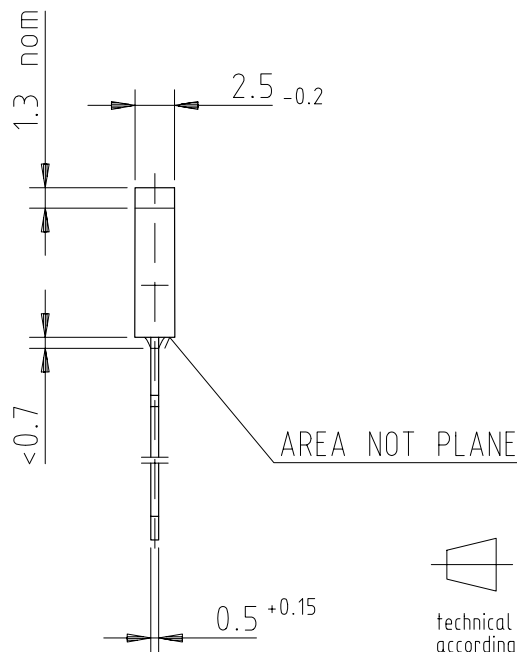
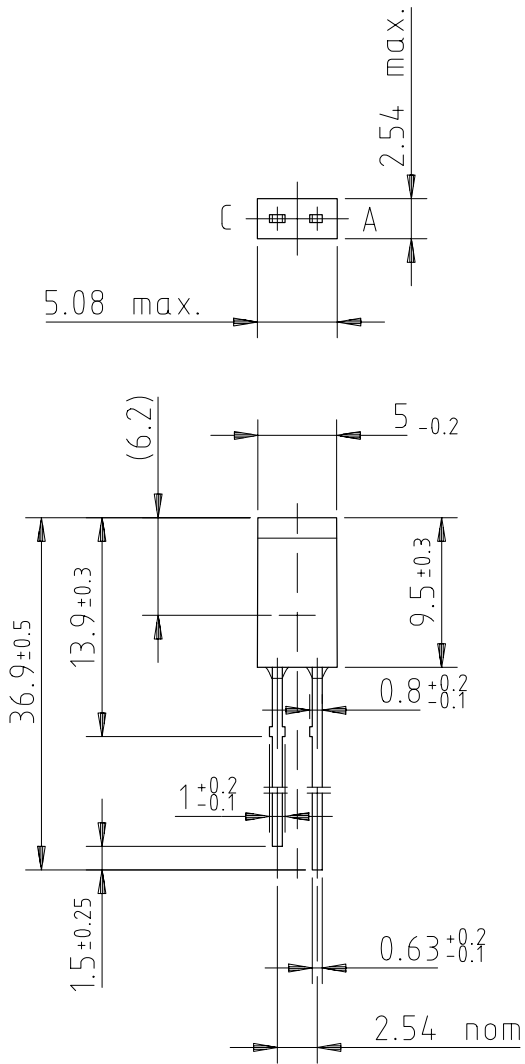


Figure 19. Relative Luminous Intensity vs. Wavelength

Dimensions in mm



95 11326

technical drawings
according to DIN
specifications



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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